

Description

Features

- 100V, 4.5A
 $R_{DS(ON)} < 295m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 330m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

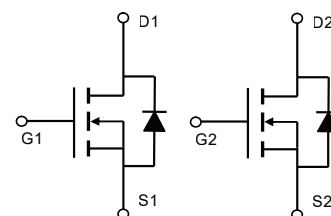
- Load Switch
- PWM Application
- Power management

100% UIS TESTED!

100% ΔV_{ds} TESTED!



DFN5x6



Schematic

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
VSM4DN10	VSM4DN10-D56	TAPING	DFN5x6	13inch	2500	25000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C = 25°C	4.5	A
		T _C = 100°C	2.9	A
I _{DM}	Pulsed Drain Current ^{note1}		18	A
EAS	Single Pulsed Avalanche Energy ^{note2}		0.6	mJ
P _D	Power Dissipation	T _C = 25°C	10	W
R _{θJC}	Thermal Resistance, Junction to Ambient		12.5	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
R _{DS(on)}	Static Drain-Source on-Resistance Note3	V _{GS} =10V, I _D =2A	-	225	295	mΩ
		V _{GS} =4.5V, I _D =1A	-	235	330	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	321	-	pF
C _{Oss}	Output Capacitance		-	21	-	pF
C _{rss}	Reverse Transfer Capacitance		-	15	-	pF
Q _g	Total Gate Charge	V _{DS} =50V, I _D =2A, V _{GS} =10V	-	11	-	nC
Q _{gs}	Gate-Source Charge		-	3	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	2.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =50V, I _D =1.8A, R _{GEN} =6Ω, V _{GS} =10V	-	7	-	ns
t _r	Turn-on Rise Time		-	10	-	ns
t _{d(off)}	Turn-off Delay Time		-	35	-	ns
t _f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	4.5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	18	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =4.5A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	T _J =25℃, I _F =2A,dI/dt=100A/μs	-	50	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	75	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=1.5A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

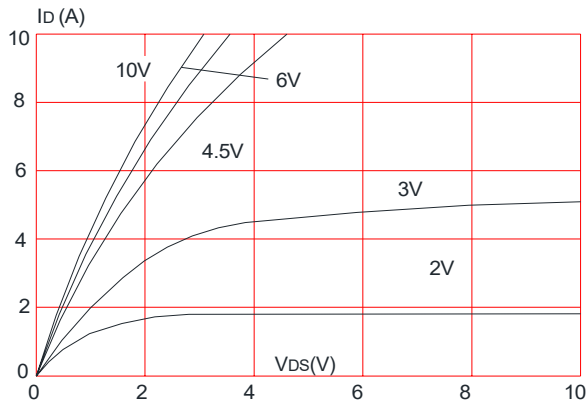
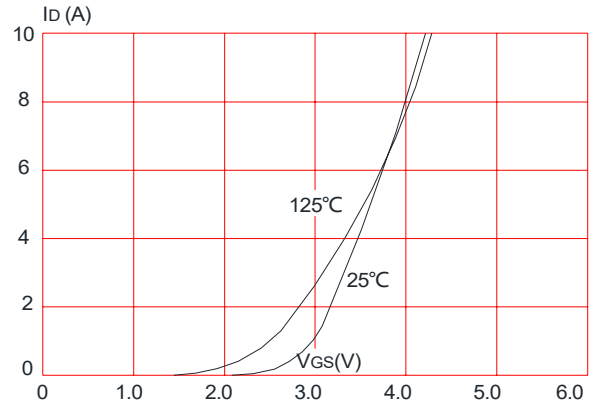
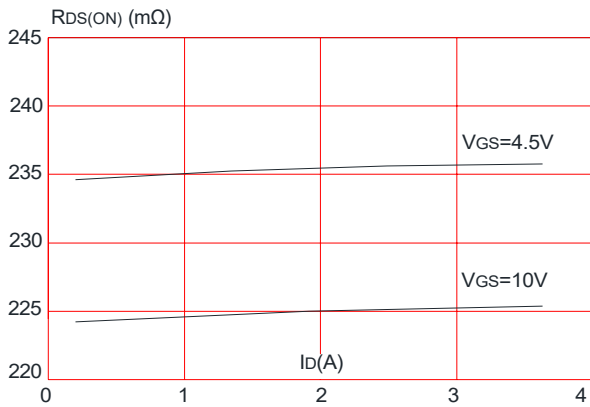
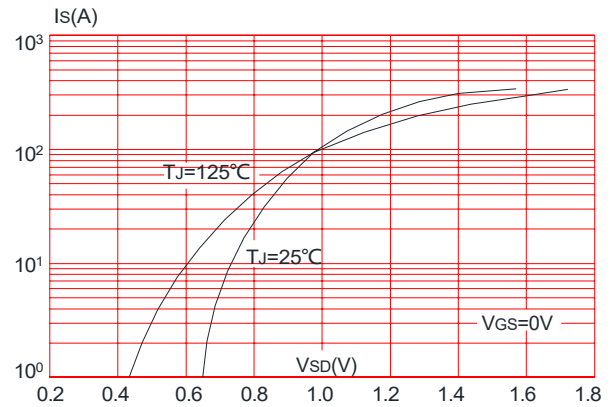
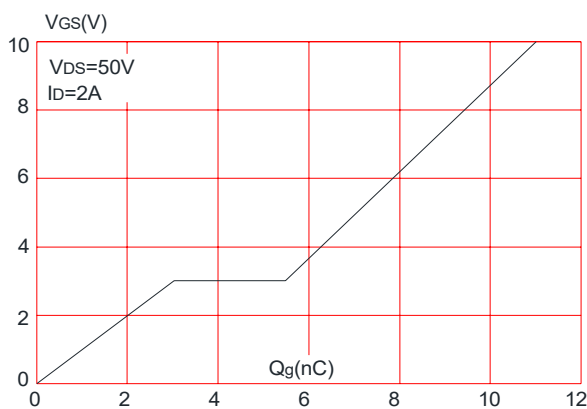
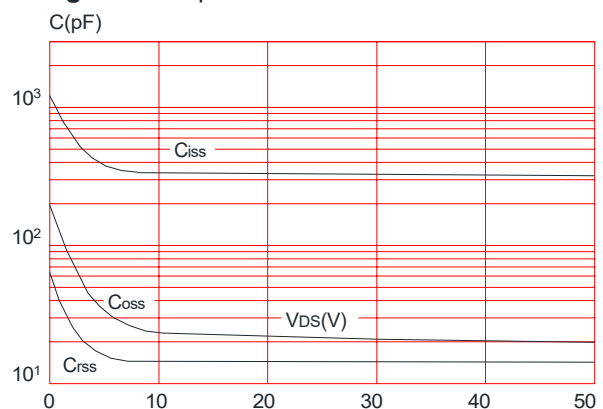
Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

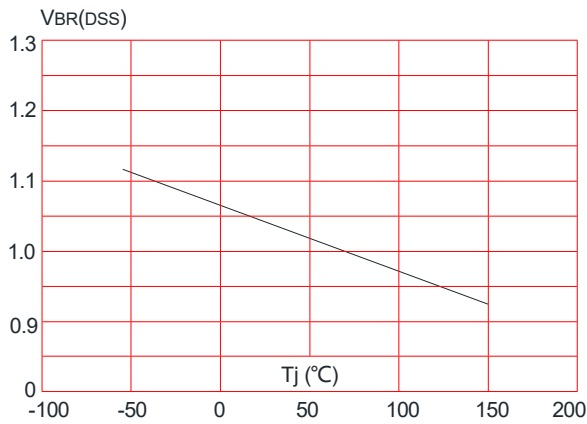


Figure 8: Normalized on Resistance vs. Junction Temperature

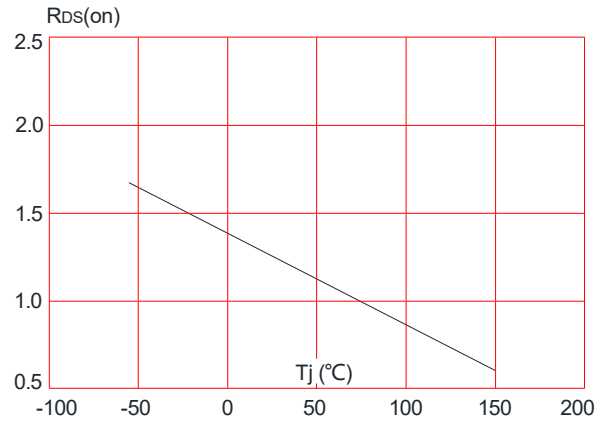


Figure 9: Maximum Safe Operating Area

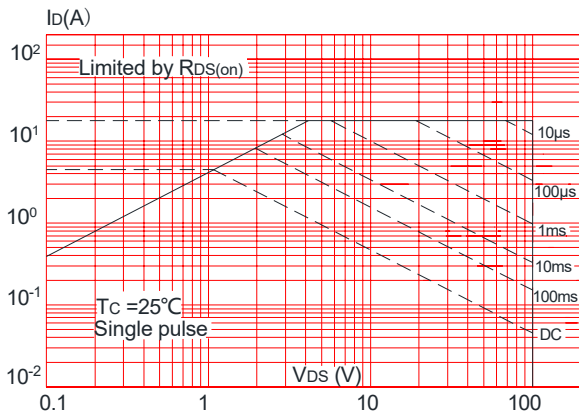


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

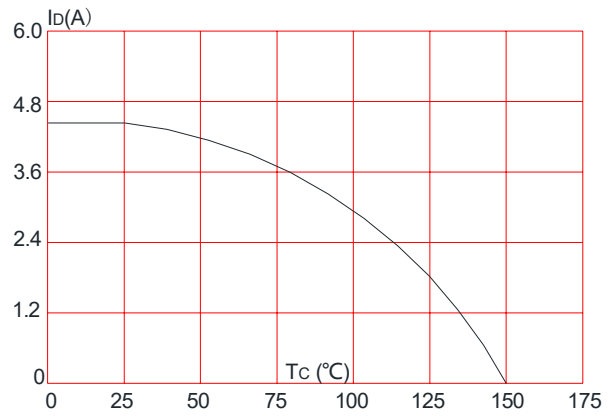
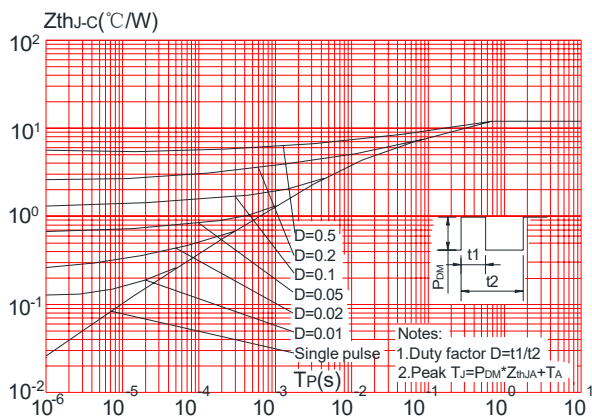


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

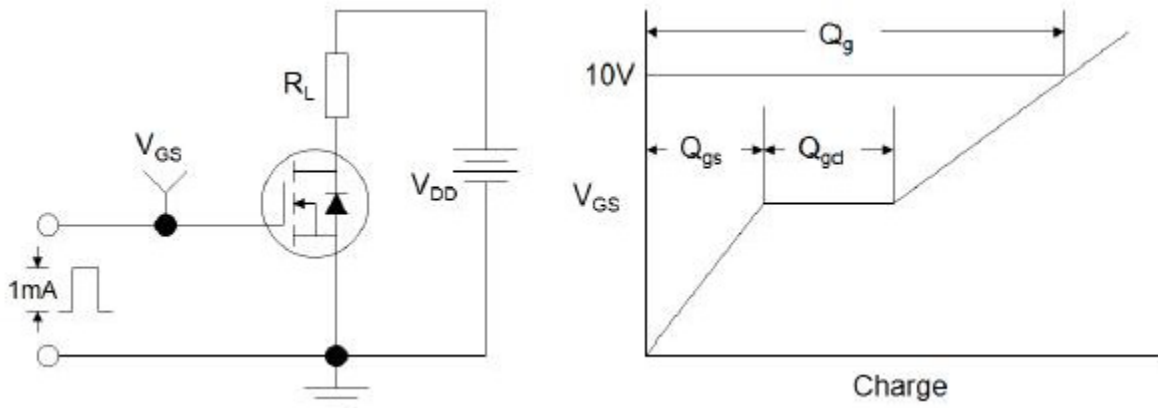


Figure1:Gate Charge Test Circuit & Waveform

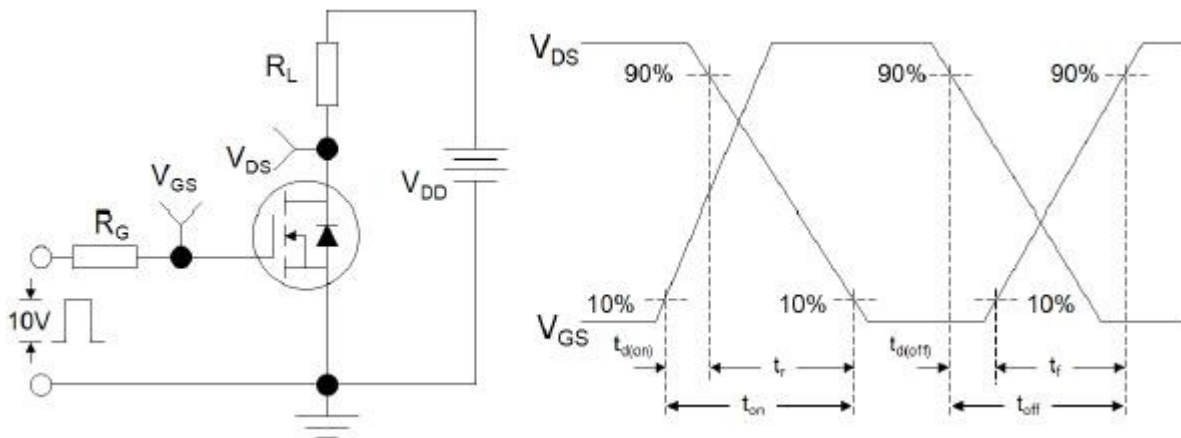


Figure 2: Resistive Switching Test Circuit & Waveforms

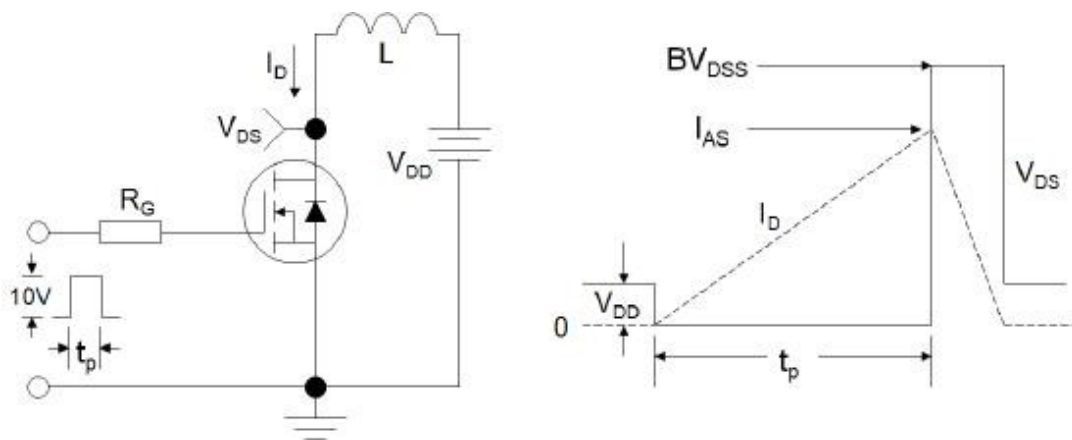


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms